MC14014B, MC14021B

8-Bit Static Shift Register

The MC14014B and MC14021B 8−bit static shift registers are constructed with MOS P−channel and N−channel enhancement mode devices in a single monolithic structure. These shift registers find primary use in parallel−to−serial data conversion, synchronous and asynchronous parallel input, serial output data queueing; and other general purpose register applications requiring low power and/or high noise immunity.

Features

- Synchronous Parallel Input/Serial Output (MC14014B)
- Asynchronous Parallel Input/Serial Output (MC14021B)
- Synchronous Serial Input/Serial Output
- Full Static Operation
- “Q” Outputs from Sixth, Seventh, and Eighth Stages
- Double Diode Input Protection
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low−power TTL Loads or One Low−power Schottky TTL Load Over the Rated Temperature Range
- MC14014B Pin−for−Pin Replacement for CD4014B
- MC14021B Pin−for−Pin Replacement for CD4021B
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- This Device is Pb−Free and is RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	−0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	−0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P_D	Power Dissipation, per Package (Note 1)	500	mW
T_A	Ambient Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8−Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

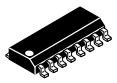
1. Temperature Derating: “D/DW” Package: –7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

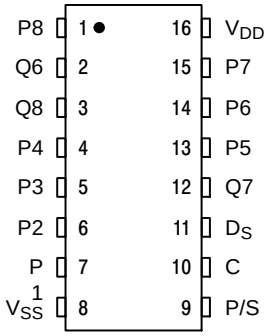
ON Semiconductor®

http://onsemi.com

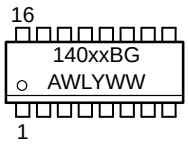


SOIC−16
D SUFFIX
CASE 751B

PIN ASSIGNMENT



MARKING DIAGRAM



xx = Specific Device Code
A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb−Free Indicator

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

© Semiconductor Components Industries, LLC, 2014

TRUTH TABLE

SERIAL OPERATION:

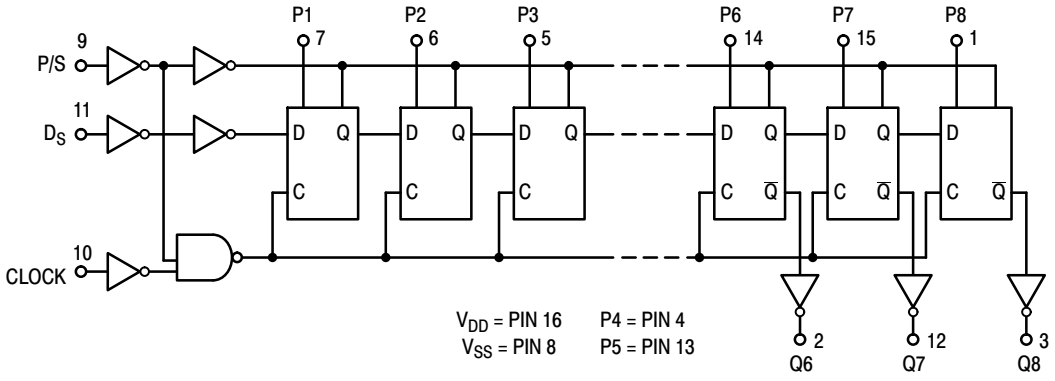
t	Clock	D_S	P/S	Q6 t=n+6	Q7 t=n+7	Q8 t=n+8
n	↗	0	0	0	?	?
n+1	↗	1	0	1	0	?
n+2	↗	0	0	0	1	0
n+3	↗	1	0	1	0	1
	↘	X	0	Q6	Q7	Q8

PARALLEL OPERATION:

Clock		D_S	P/S	P_n	$*Q_n$
MC14014B	MC14021B				
↗	X	X	1	0	0
↗	X	X	1	1	1

*Q6, Q7, & Q8 are available externally
X = Don't Care

LOGIC DIAGRAM



ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	−55°C Min	−55°C Max	25°C Min	25°C Typ (Note 2)	25°C Max	125°C Min	125°C Max	Unit
Output Voltage “0” Level	V_{OL}	5.0	−	0.05	−	0	0.05	−	0.05	Vdc
V_{in} = V_{DD} or 0		10	−	0.05	−	0	0.05	−	0.05	
		15	−	0.05	−	0	0.05	−	0.05	
V_{in} = 0 or V_{DD} “1” Level	V_{OH}	5.0	4.95	−	4.95	5.0	−	4.95	−	Vdc
		10	9.95	−	9.95	10	−	9.95	−	
		15	14.95	−	14.95	15	−	14.95	−	
Input Voltage “0” Level	V_{IL}									Vdc
(V_O = 4.5 or 0.5 Vdc)		5.0	−	1.5	−	2.25	1.5	−	1.5	
(V_O = 9.0 or 1.0 Vdc)		10	−	3.0	−	4.50	3.0	−	3.0	
(V_O = 13.5 or 1.5 Vdc)		15	−	4.0	−	6.75	4.0	−	4.0	
(V_O = 0.5 or 4.5 Vdc) “1” Level	V_{IH}	5.0	3.5	−	3.5	2.75	−	3.5	−	Vdc
(V_O = 1.0 or 9.0 Vdc)		10	7.0	−	7.0	5.50	−	7.0	−	
(V_O = 1.5 or 13.5 Vdc)		15	11	−	11	8.25	−	11	−	
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		5.0	–3.0	−	–2.4	–4.2	−	–1.7	−	
(V_{OH} = 4.6 Vdc)		5.0	–0.64	−	–0.51	–0.88	−	−0.36	−	
(V_{OH} = 9.5 Vdc)		10	–1.6	−	−1.3	–2.25	−	–0.9	−	
(V_{OH} = 13.5 Vdc)		15	–4.2	−	−3.4	−8.8	−	−2.4	−	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	5.0	0.64	−	0.51	0.88	−	0.36	−	mAdc
(V_{OL} = 0.5 Vdc)		10	1.6	−	1.3	2.25	−	0.9	−	
(V_{OL} = 1.5 Vdc)		15	4.2	−	3.4	8.8	−	2.4	−	
Input Current	I_{in}	15	−	±0.1	−	±0.00001	±0.1	−	±1.0	μAdc
Input Capacitance (V_{in} = 0)	C_{in}	−	−	−	−	5.0	7.5	−	−	pF
Quiescent Current (Per Package)	I_{DD}	5.0	−	5.0	−	0.005	5.0	−	150	μAdc
		10	−	10	−	0.010	10	−	300	
		15	−	15	−	0.015	15	−	600	
Total Supply Current (Notes 3 & 4) (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0	I_T = (0.75 μA/kHz) f + I_{DD}							μAdc
		10	I_T = (1.50 μA/kHz) f + I_{DD}							
		15	I_T = (2.25 μA/kHz) f + I_{DD}							

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
3. The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

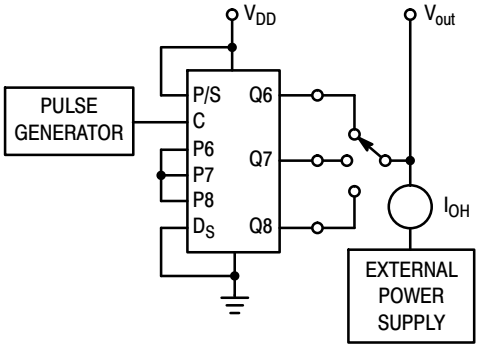
$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in μA (per package), C_L in pF, V = (V_{DD} − V_{SS}) in volts, f in kHz is input frequency, and k = 0.0015.

SWITCHING CHARACTERISTICS (Note 5) (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise and Fall Time	t_{TLH},					ns
t_{TLH}, t_{THL} = (1.5 ns/pF) C_L + 25 ns	t_{THL}	5.0	–	100	200	
t_{TLH}, t_{THL} = (0.75 ns/pF) C_L + 12.5 ns		10	–	50	100	
t_{TLH}, t_{THL} = (0.55 ns/pF) C_L + 9.5 ns		15	–	40	80	
Propagation Delay Time (Clock to Q, P/S to Q)	t_{PLH},					ns
t_{PHL}, t_{PLH} = (1.7 ns/pF) C_L + 315 ns	t_{PHL}	5.0	–	400	800	
t_{PHL}, t_{PLH} = (0.66 ns/pF) C_L + 137 ns		10	–	170	340	
t_{PHL}, t_{PLH} = (0.5 ns/pF) C_L + 90 ns		15	–	115	230	
Clock Pulse Width	t_{WH}	5.0	400	150	–	ns
		10	175	75	–	
		15	135	40	–	
Clock Frequency	f_{cl}	5.0	–	3.0	1.5	MHz
		10	–	6.0	3.0	
		15	–	8.0	4.0	
Parallel/Serial Control Pulse Width	t_{WH}	5.0	400	150	–	ns
		10	175	75	–	
		15	135	40	–	
Setup Time	t_{su}	5.0	200	100	–	ns
P/S to Clock		10	100	50	–	
		15	80	40	–	
Hold Time	t_h	5.0	20	– 2.5	–	ns
Clock to P/S		10	20	– 10	–	
		15	25	0	–	
Setup Time	t_{su}	5.0	350	150	–	ns
Data (Parallel or Serial) to		10	80	50	–	
Clock or P/S		15	60	30	–	
Hold Time	t_h	5.0	45	0	–	ns
Clock to D_S		10	35	0	–	
		15	35	5	–	
Hold Time	t_h	5.0	50	25	–	ns
Clock to P_n		10	45	20	–	
		15	45	20	–	
Input Clock Rise Time	$t_{r(cl)}$	5.0	–	–	15	μs
		10	–	–	5	
		15	–	–	4	

5. The formulas given are for the typical characteristics only at 25°C.
6. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.



Preset output under test to a logic “1” level.

Figure 1. Output Source Current Test Circuit

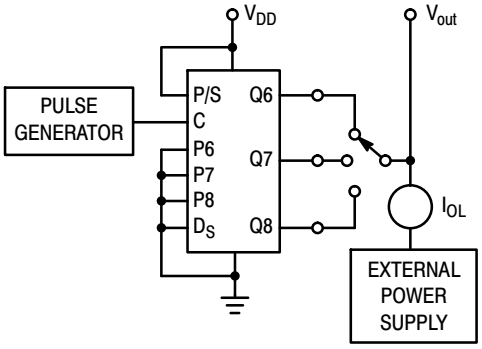


Figure 2. Output Sink Current Test Circuit

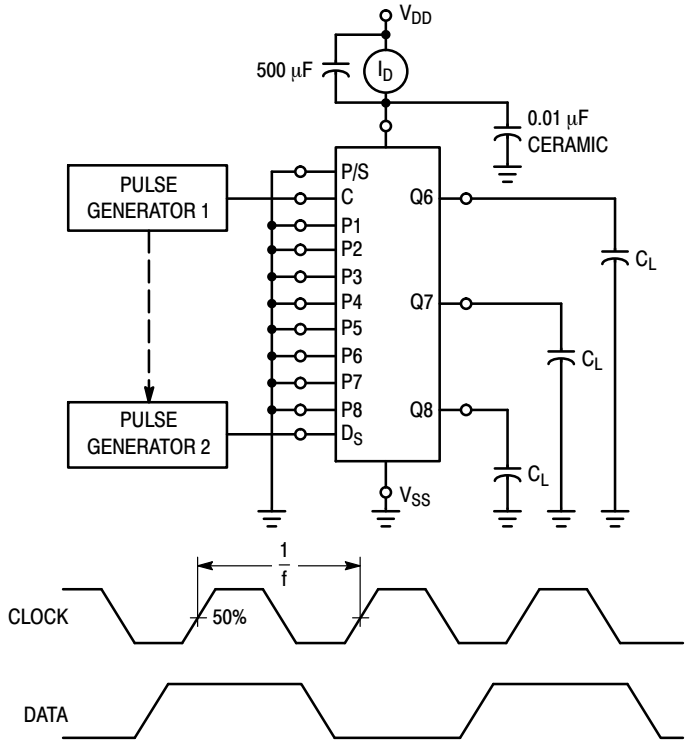


Figure 3. Power Dissipation Test Circuit and Waveform

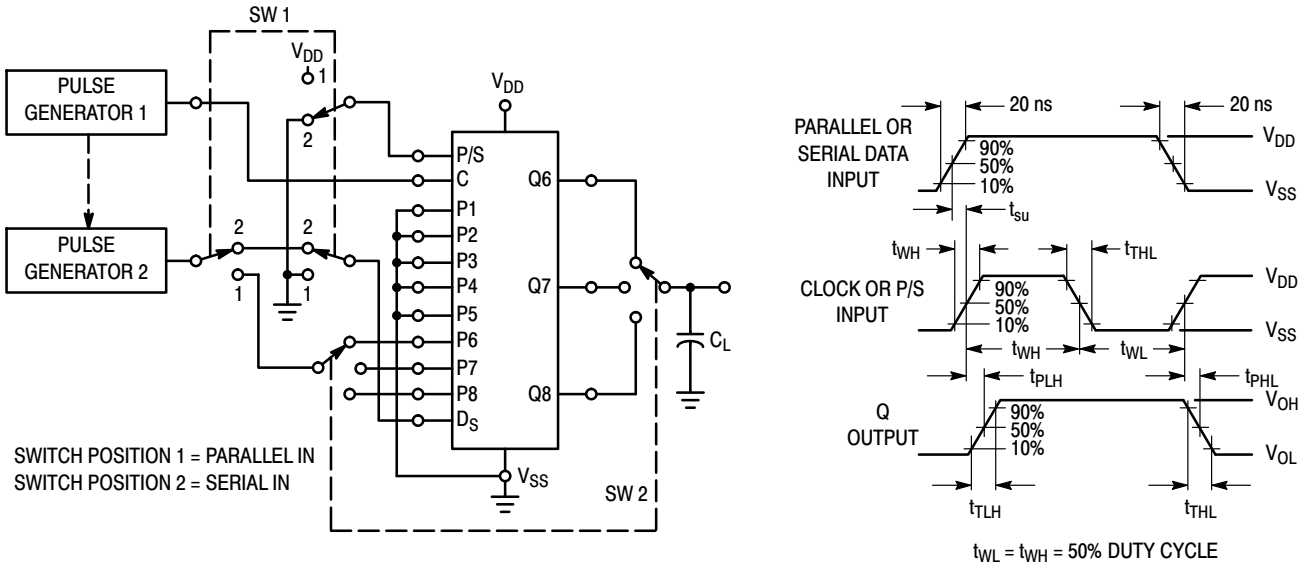


Figure 4. Switching Time Test Circuit and Waveforms

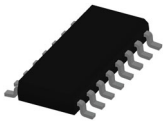
ORDERING INFORMATION

Device	Package	Shipping†
MC14014BDG	SOIC−16 (Pb−Free)	48 Units / Rail
MC14014BDR2G	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
NLV14014BDR2G*	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
MC14021BDG	SOIC−16 (Pb−Free)	48 Units / Rail
MC14021BDR2G	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
NLV14021BDR2G*	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

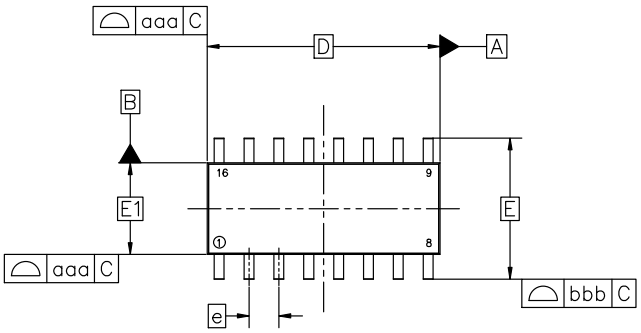
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



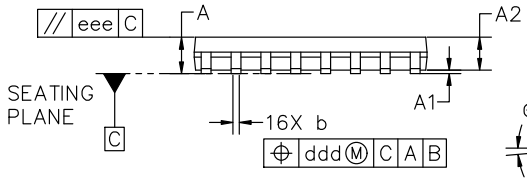
SOIC−16 9.90x3.90x1.50 1.27P
CASE 751B
ISSUE L

DATE 29 MAY 2024

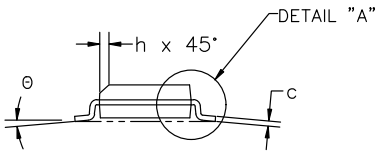
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.



TOP VIEW

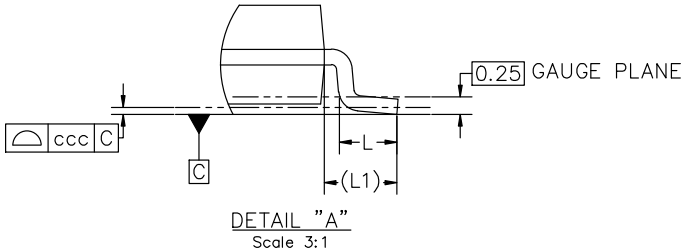


SIDE VIEW

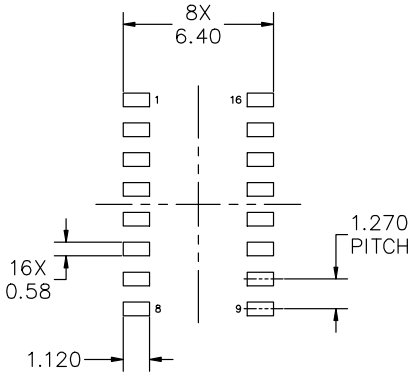


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.00	0.05	0.10
A2	1.35	1.50	1.65
b	0.35	0.42	0.49
c	0.19	0.22	0.25
D	9.90 BSC		
E	6.00 BSC		
E1	3.90 BSC		
e	1.27 BSC		
h	0.25	−−−	0.50
L	0.40	0.83	1.25
L1	1.05 REF		
θ	0°	−−−	7°
TOLERANCE OF FORM AND POSITION			
aaa	0.10		
bbb	0.20		
ccc	0.10		
ddd	0.25		
eee	0.10		



DETAIL "A"
Scale 3:1



RECOMMENDED MOUNTING FOOTPRINT

*FOR ADDITIONAL INFORMATION ON OUR PB−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE onsemi SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D

DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC−16 9.90X3.90X1.50 1.27P	PAGE 1 OF 2

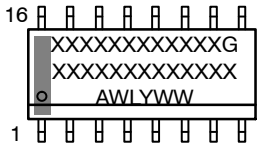
onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2019

SOIC−16 9.90x3.90x1.50 1.27P
CASE 751B
ISSUE L

DATE 29 MAY 2024

GENERIC
MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1

STYLE 5:		STYLE 6:		STYLE 7:	
PIN 1.	DRAIN, DYE #1	PIN 1.	CATHODE	PIN 1.	SOURCE N-CH
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT)
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT)
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT)
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT)
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPUT)
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT)
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT)
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT)
13.	GATE, #2	13.	ANODE	13.	GATE N-CH
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT)
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT)
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2019

onsemi, , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales